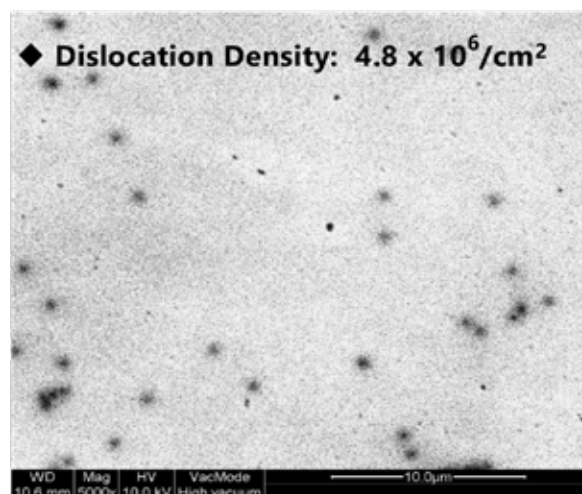
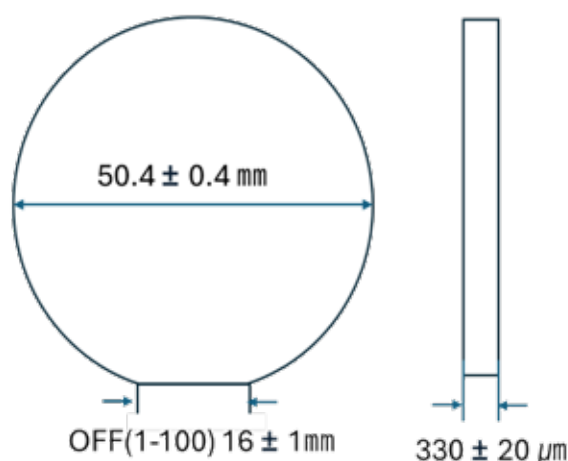


GaN 2"Free-standing N-Type Wafer



◆ Typical specifications of GaN wafer

Properties	Typical Specifications
Material	GaN
Diameter	50.4 mm ± 0.4mm
Thickness	330 μm ± 20 μm
Orientation	C-plane (0001) 0.4° off ± 0.15°
FWHM of X-ray Rocking Curve (ω-scan)	< 100 arcsec for (002) < 100 arcsec for (102)
Dislocation Density (by CL)	$\leq 7 \times 10^6/\text{cm}^2$
Conduction type	N-type
Carrier Concentration	$> 1 \times 10^{17}/\text{cm}^3$
Surface Roughness(R_a) (by AFM 5 μm x 5 μm scan)	< 0.5 nm
Backside finish	Rough/ Etched surface
Marco Defects (> Φ 50 μm)	< 50 ea/ 2inch (< 2.5 ea/cm ²)
Edge Excursion Zone	< 3 mm